

# BC337, BC337-25, BC337-40

## Amplifier Transistors

### NPN Silicon

#### Features

- These are Pb-Free Devices

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	45	Vdc
Collector – Base Voltage	$V_{CBO}$	50	Vdc
Emitter – Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current – Continuous	$I_C$	800	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

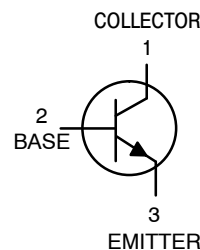
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

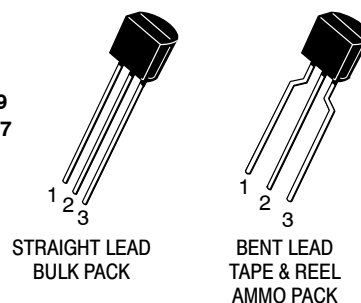


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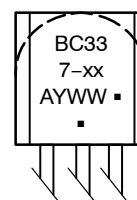
<http://onsemi.com>



TO-92  
CASE 29  
STYLE 17



#### MARKING DIAGRAM



BC337-xx = Device Code  
(Refer to page 4)

A = Assembly Location

Y = Year

WW = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# BC337, BC337-25, BC337-40

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector - Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	45	-	-	Vdc
Collector - Emitter Breakdown Voltage ( $I_C = 100\ \mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CES}$	50	-	-	Vdc
Emitter - Base Breakdown Voltage ( $I_E = 10\ \mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	5.0	-	-	Vdc
Collector Cutoff Current ( $V_{CB} = 30\text{ V}$ , $I_E = 0$ )	$I_{CBO}$	-	-	100	nAdc
Collector Cutoff Current ( $V_{CE} = 45\text{ V}$ , $V_{BE} = 0$ )	$I_{CES}$	-	-	100	nAdc
Emitter Cutoff Current ( $V_{EB} = 4.0\text{ V}$ , $I_C = 0$ )	$I_{EBO}$	-	-	100	nAdc

## ON CHARACTERISTICS

DC Current Gain ( $I_C = 100\text{ mA}$ , $V_{CE} = 1.0\text{ V}$ )  ( $I_C = 300\text{ mA}$ , $V_{CE} = 1.0\text{ V}$ )	BC337 BC337-25 BC337-40	$h_{FE}$	100	-	630	-
			160	-	400	
			250	-	630	
			60	-	-	
Base-Emitter On Voltage ( $I_C = 300\text{ mA}$ , $V_{CE} = 1.0\text{ V}$ )	$V_{BE(on)}$	-	-	1.2	Vdc	
Collector - Emitter Saturation Voltage ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )	$V_{CE(sat)}$	-	-	0.7	Vdc	

## SMALL-SIGNAL CHARACTERISTICS

Output Capacitance ( $V_{CB} = 10\text{ V}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ob}$	-	15	-	pF
Current - Gain - Bandwidth Product ( $I_C = 10\text{ mA}$ , $V_{CE} = 5.0\text{ V}$ , $f = 100\text{ MHz}$ )	$f_T$	-	210	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

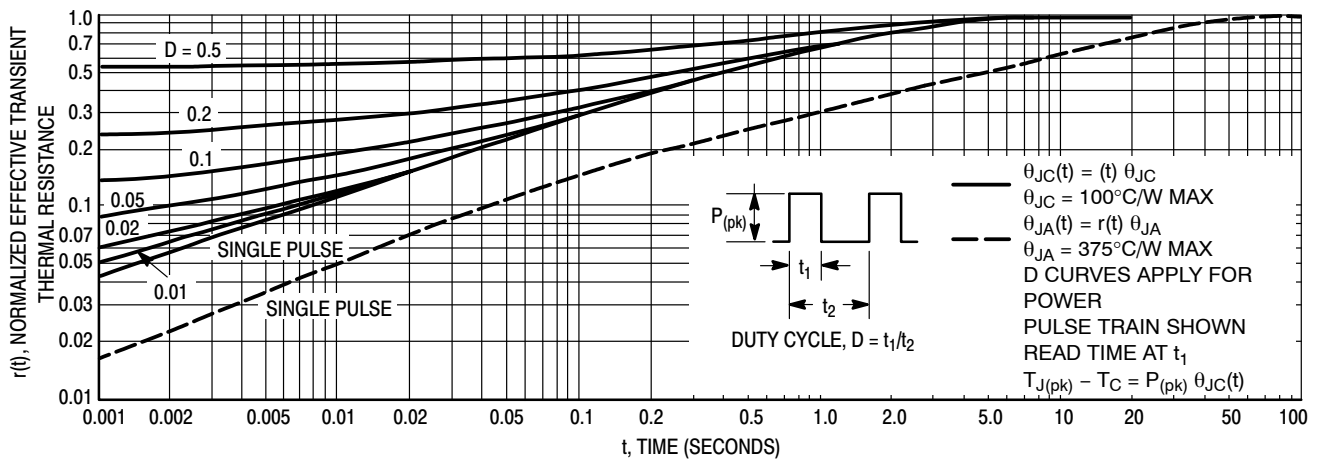


Figure 1. Thermal Response

BC337, BC337-25, BC337-40

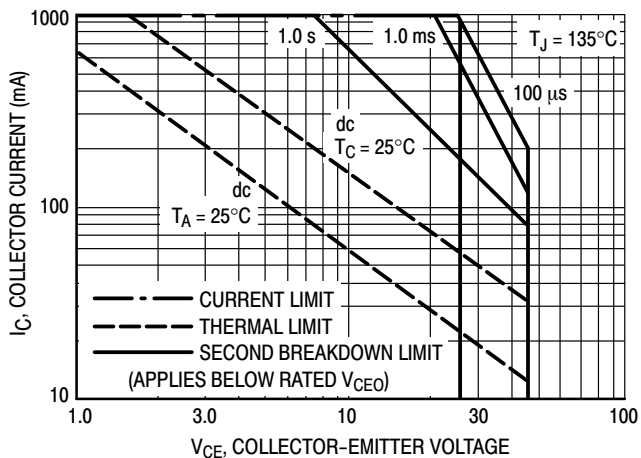


Figure 2. Active Region - Safe Operating Area

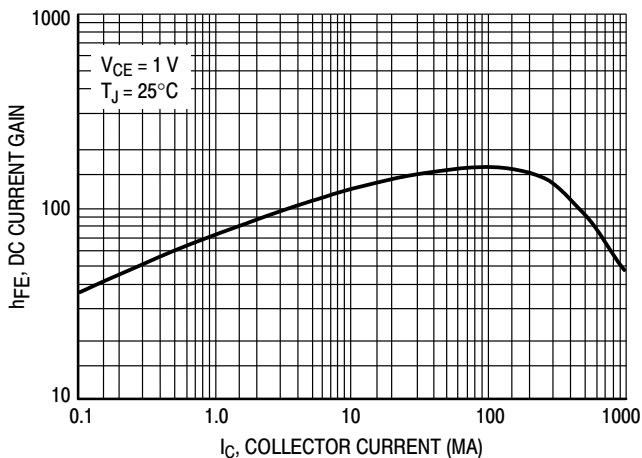


Figure 3. DC Current Gain

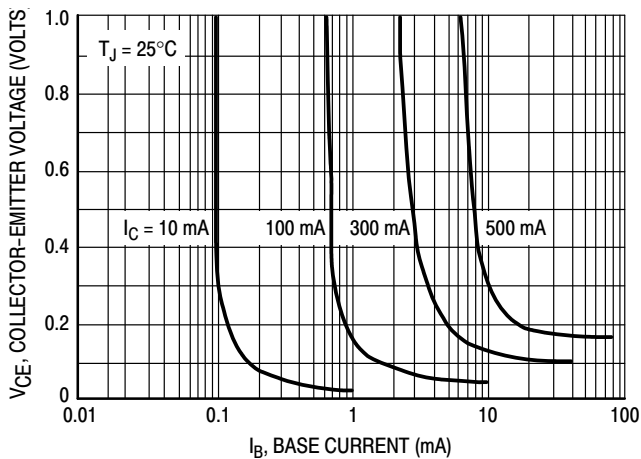


Figure 4. Saturation Region

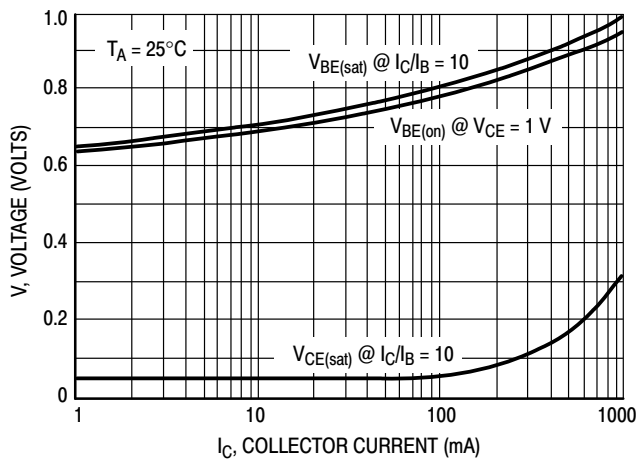


Figure 5. "On" Voltages

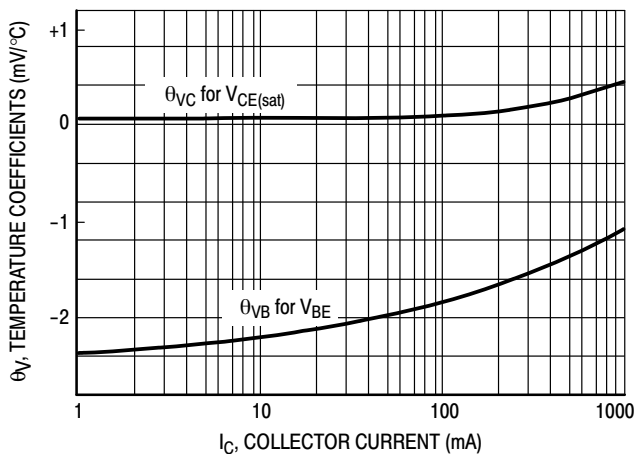


Figure 6. Temperature Coefficients

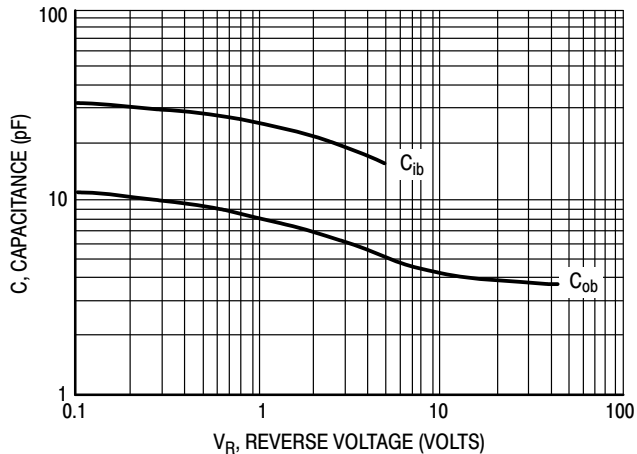


Figure 7. Capacitances

## BC337, BC337-25, BC337-40

### ORDERING INFORMATION

Device	Marking	Package	Shipping†
BC337G	7	TO-92 (Pb-Free)	5000 Units / Bulk
BC337RL1G	7		2000 / Tape & Reel
BC337-025G	7-25		5000 Units / Bulk
BC337-25RL1G	7-25		2000 / Tape & Reel
BC337-25RLRAG	7-25		2000 / Tape & Reel
BC337-25ZL1G	7-25		2000 / Ammo Box
BC337-040G	7-40		5000 Units / Bulk
BC337-40RL1G	7-40		2000 / Tape & Reel
BC337-40ZL1G	7-40		2000 / Ammo Box

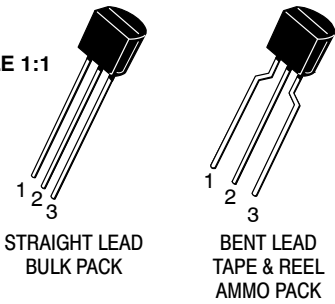
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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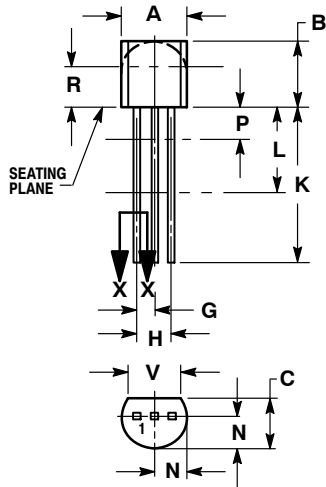


SCALE 1:1

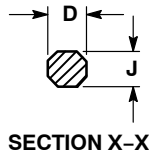


TO-92 (TO-226)  
CASE 29-11  
ISSUE AM

DATE 09 MAR 2007



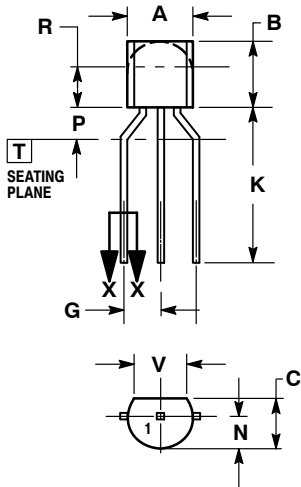
STRAIGHT LEAD  
BULK PACK



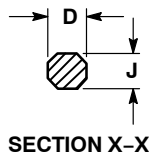
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLES ON PAGE 2

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**TO-92 (TO-226)**  
**CASE 29-11**  
**ISSUE AM**

DATE 09 MAR 2007

STYLE 1:  
 PIN 1. EMITTER  
 2. BASE  
 3. COLLECTOR

STYLE 2:  
 PIN 1. BASE  
 2. EMITTER  
 3. COLLECTOR

STYLE 3:  
 PIN 1. ANODE  
 2. ANODE  
 3. CATHODE

STYLE 4:  
 PIN 1. CATHODE  
 2. CATHODE  
 3. ANODE

STYLE 5:  
 PIN 1. DRAIN  
 2. SOURCE  
 3. GATE

STYLE 6:  
 PIN 1. GATE  
 2. SOURCE & SUBSTRATE  
 3. DRAIN

STYLE 7:  
 PIN 1. SOURCE  
 2. DRAIN  
 3. GATE

STYLE 8:  
 PIN 1. DRAIN  
 2. GATE  
 3. SOURCE & SUBSTRATE

STYLE 9:  
 PIN 1. BASE 1  
 2. EMITTER  
 3. BASE 2

STYLE 10:  
 PIN 1. CATHODE  
 2. GATE  
 3. ANODE

STYLE 11:  
 PIN 1. ANODE  
 2. CATHODE & ANODE  
 3. CATHODE

STYLE 12:  
 PIN 1. MAIN TERMINAL 1  
 2. GATE  
 3. MAIN TERMINAL 2

STYLE 13:  
 PIN 1. ANODE 1  
 2. GATE  
 3. CATHODE 2

STYLE 14:  
 PIN 1. EMITTER  
 2. COLLECTOR  
 3. BASE

STYLE 15:  
 PIN 1. ANODE 1  
 2. CATHODE  
 3. ANODE 2

STYLE 16:  
 PIN 1. ANODE  
 2. GATE  
 3. CATHODE

STYLE 17:  
 PIN 1. COLLECTOR  
 2. BASE  
 3. EMITTER

STYLE 18:  
 PIN 1. ANODE  
 2. CATHODE  
 3. NOT CONNECTED

STYLE 19:  
 PIN 1. GATE  
 2. ANODE  
 3. CATHODE

STYLE 20:  
 PIN 1. NOT CONNECTED  
 2. CATHODE  
 3. ANODE

STYLE 21:  
 PIN 1. COLLECTOR  
 2. EMITTER  
 3. BASE

STYLE 22:  
 PIN 1. SOURCE  
 2. GATE  
 3. DRAIN

STYLE 23:  
 PIN 1. GATE  
 2. SOURCE  
 3. DRAIN

STYLE 24:  
 PIN 1. EMITTER  
 2. COLLECTOR/ANODE  
 3. CATHODE

STYLE 25:  
 PIN 1. MT 1  
 2. GATE  
 3. MT 2

STYLE 26:  
 PIN 1. V<sub>CC</sub>  
 2. GROUND 2  
 3. OUTPUT

STYLE 27:  
 PIN 1. MT  
 2. SUBSTRATE  
 3. MT

STYLE 28:  
 PIN 1. CATHODE  
 2. ANODE  
 3. GATE

STYLE 29:  
 PIN 1. NOT CONNECTED  
 2. ANODE  
 3. CATHODE

STYLE 30:  
 PIN 1. DRAIN  
 2. GATE  
 3. SOURCE

STYLE 31:  
 PIN 1. GATE  
 2. DRAIN  
 3. SOURCE

STYLE 32:  
 PIN 1. BASE  
 2. COLLECTOR  
 3. EMITTER

STYLE 33:  
 PIN 1. RETURN  
 2. INPUT  
 3. OUTPUT

STYLE 34:  
 PIN 1. INPUT  
 2. GROUND  
 3. LOGIC

STYLE 35:  
 PIN 1. GATE  
 2. COLLECTOR  
 3. EMITTER

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